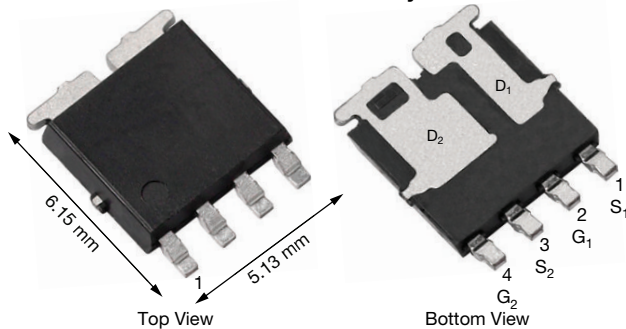


Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFETs

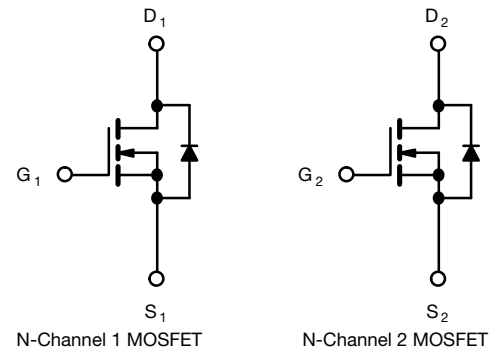
PowerPAK® SO-8L Dual Asymmetric

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V _{DS} (V)	60	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0355	0.0155
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.0480	0.0200
I _D (A)	15	40
Configuration	Dual N	
Package	PowerPAK SO-8L Dual Asymmetric	



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-source voltage	V _{DS}	60	60	V
Gate-source voltage	V _{GS}	± 20		
Continuous drain current	I _D	T _C = 25 °C	15 ^a	A
		T _C = 125 °C	11	
Continuous source current (diode conduction)	I _S	15 ^a	44	A
Pulsed drain current ^b	I _{DM}	30	70	
Single pulse avalanche current	I _{AS}	12	20	mJ
Single pulse avalanche energy	E _{AS}	7.2	20	
Maximum power dissipation ^b	P _D	T _C = 25 °C	27	W
		T _C = 125 °C	9	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175		°C
Soldering recommendations (peak temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-ambient	R _{thJA}	85	85	°C/W
Junction-to-case (drain)	R _{thJC}	5.5	3.1	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT	
Static									
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	60	-	-	V	
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	60	-	-		
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	1.5	2.0	2.5		
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	1.5	2.0	2.5		
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		N-Ch 1	-	-	± 100	nA	
				N-Ch 2	-	-	± 100		
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 1	-	-	1	μA	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	N-Ch 2	-	-	1		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	250		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	250		
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 1	10	-	-	A	
		$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 2	20	-	-		
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}$	N-Ch 1	-	0.0295	0.0355	Ω	
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}$	N-Ch 2	-	0.0126	0.0155		
		$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0563		
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0253		
		$V_{GS} = 10\text{ V}$	$I_D = 2\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	0.0700		
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	0.0311		
		$V_{GS} = 4.5\text{ V}$	$I_D = 1\text{ A}$	N-Ch 1	-	0.0400	0.0480		
		$V_{GS} = 4.5\text{ V}$	$I_D = 3\text{ A}$	N-Ch 2	-	0.0165	0.0200		
Dynamic ^b									
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	410	550	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	967	1260		
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	212	280	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	436	570		
Reverse transfer capacitance	C_{rss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	15	20	pF	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	18	25		
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	6.5	10	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	14.5	23		
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	1.4	-	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	2.7	-		
Gate-drain charge ^c	Q_{gd}	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 1\text{ A}$	N-Ch 1	-	0.9	-	nC	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	N-Ch 2	-	2.1	-		
Gate resistance	R_g	$f = 1\text{ MHz}$			N-Ch 1	0.7	1.47	2.2	Ω
					N-Ch 2	0.3	0.62	0.95	



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Dynamic ^b							
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	9	15	ns
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	13	20	
Rise time ^c	t _r	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	3	5	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	3	5	
Turn-off delay time ^c	t _{d(off)}	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	15	25	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	23	35	
Fall time ^c	t _f	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	10	15	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	10	15	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}		N-Ch 1	-	-	30	A
			N-Ch 2	-	-	70	
Forward voltage	V _{SD}	I _F = 2 A, V _{GS} = 0 V	N-Ch 1	-	0.81	1.2	V
		I _F = 5 A, V _{GS} = 0 V	N-Ch 2	-	0.80	1.2	
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	24	50	ns
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	36	75	
Body diode reverse recovery charge	Q _{rr}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	17	35	nC
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	30	60	
Reverse recovery fall time	t _a	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	12	-	ns
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	19	-	
Reverse recovery rise time	t _b	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	12	-	
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	17	-	
Body diode peak reverse recovery current	I _{RM(REC)}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	-1.3	-	A
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	-1.6	-	

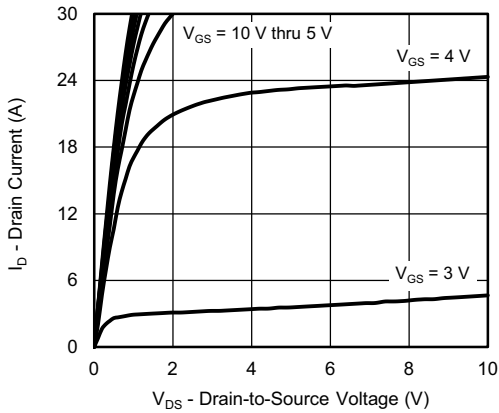
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

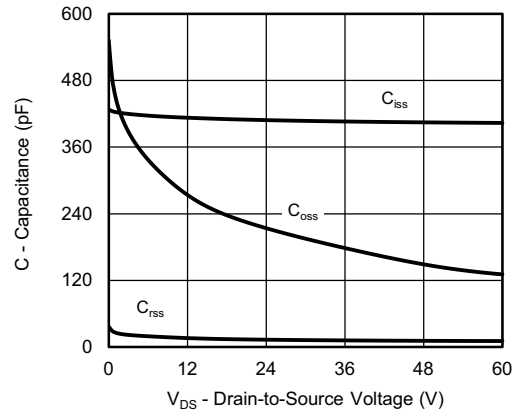
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



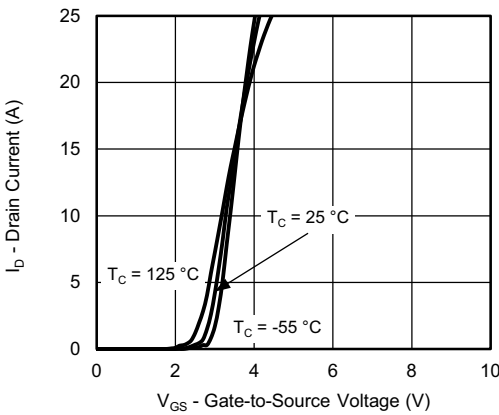
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



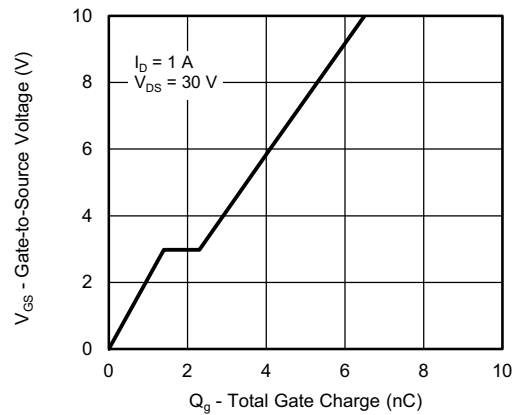
Output Characteristics



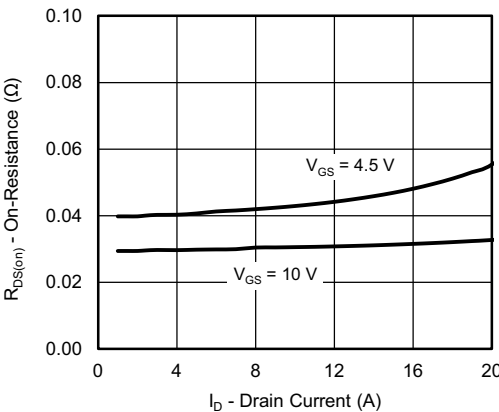
Capacitance



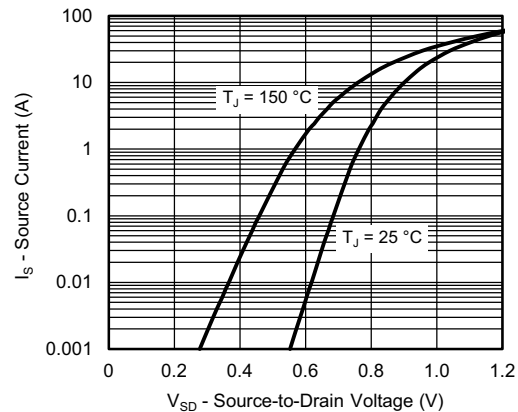
Transfer Characteristics



Gate Charge

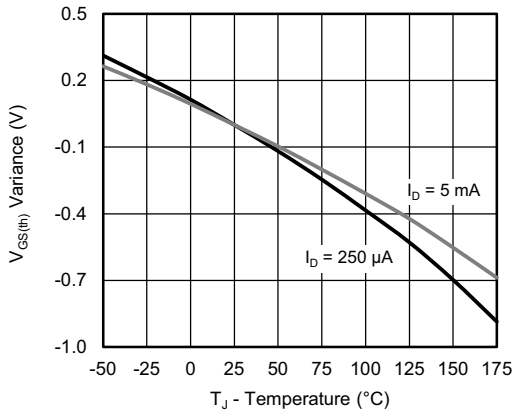


On-Resistance vs. Drain Current

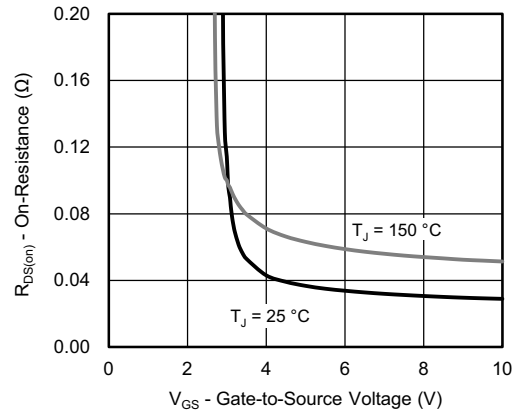


Source Drain Diode Forward Voltage

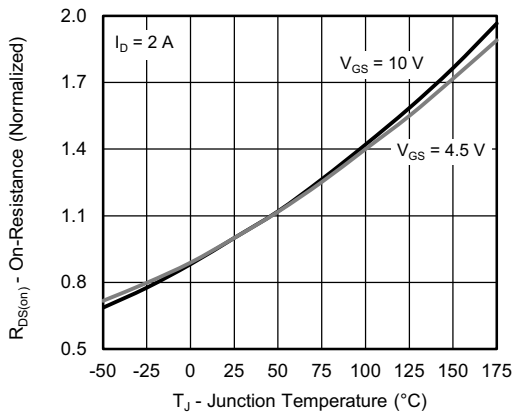
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



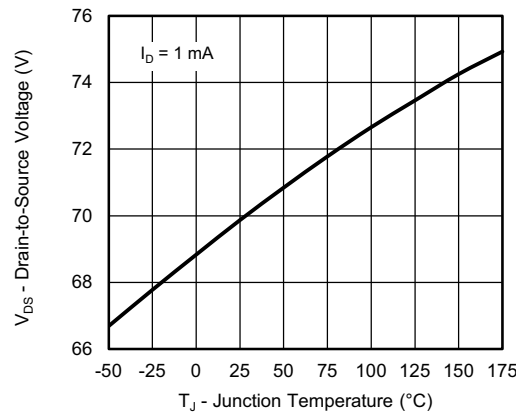
Threshold Voltage



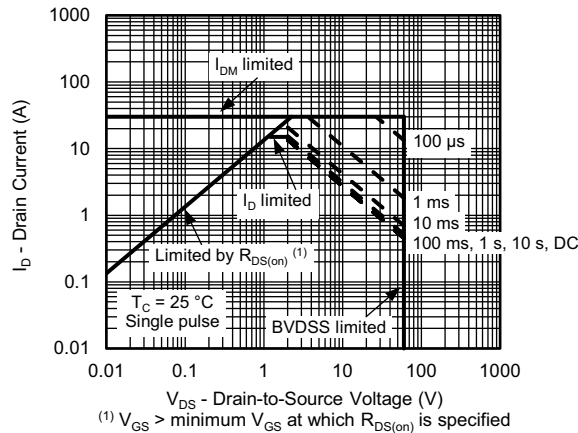
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



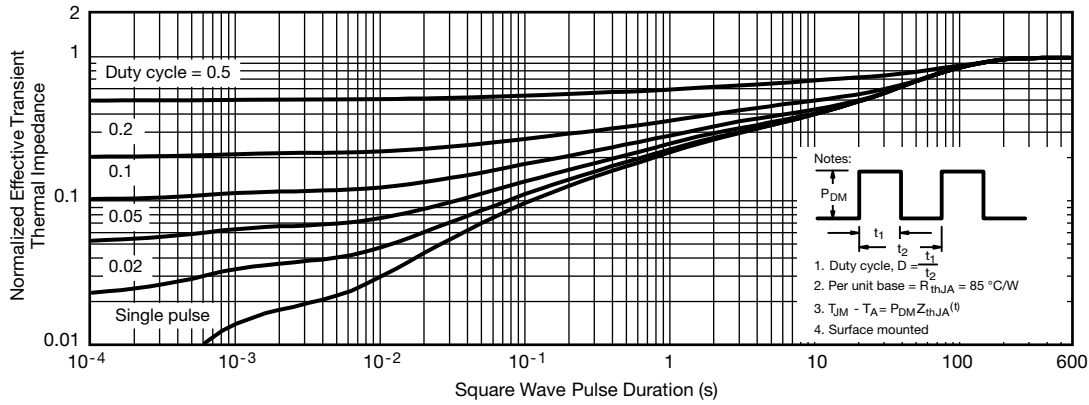
Drain Source Breakdown vs. Junction Temperature



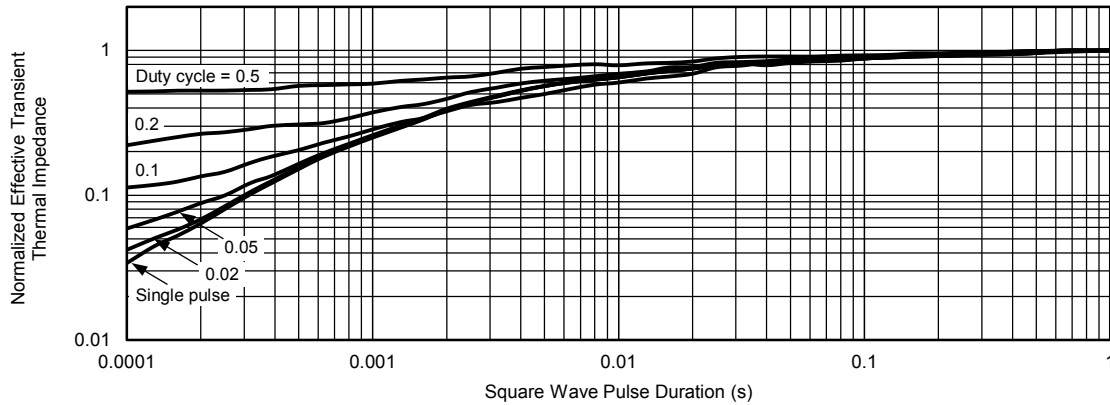
Safe Operating Area



N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



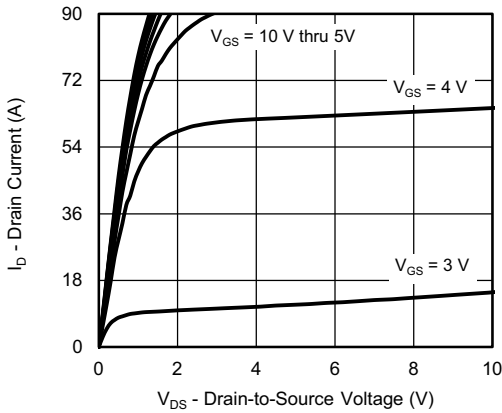
Normalized Thermal Transient Impedance, Junction-to-Case

Note

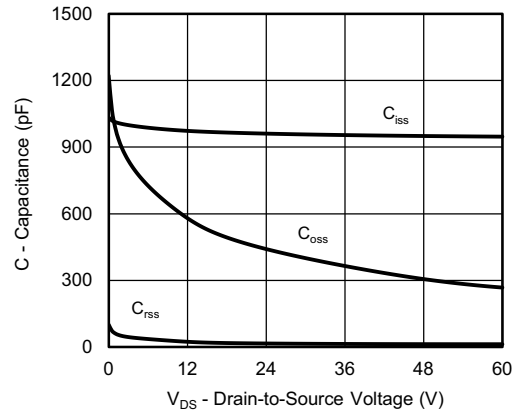
- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions



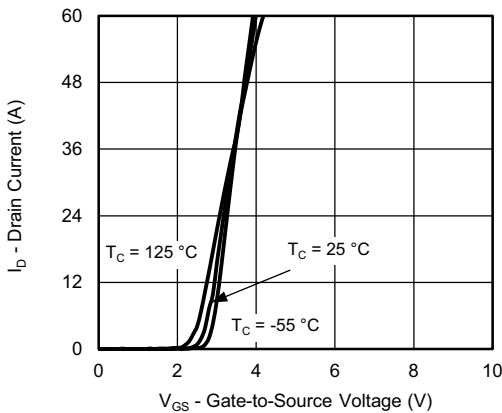
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



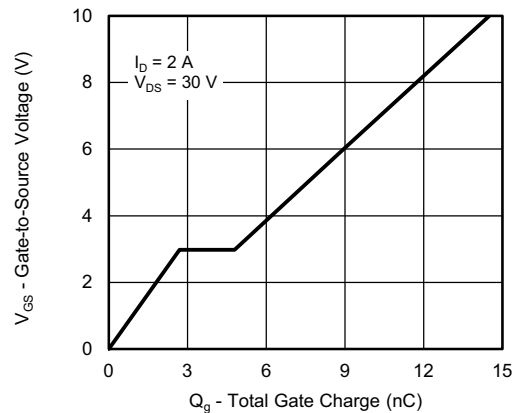
Output Characteristics



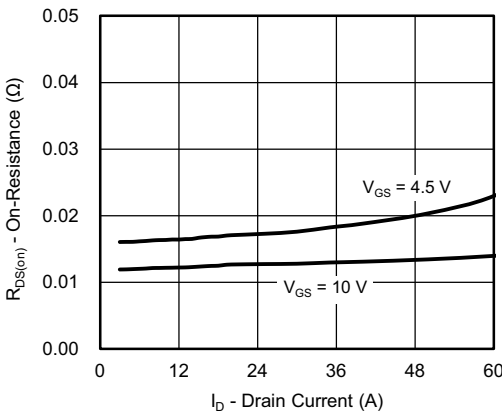
Capacitance



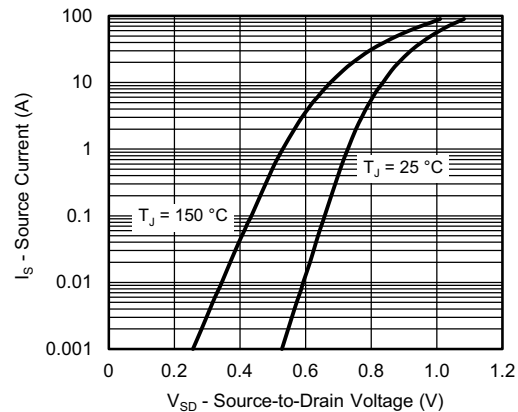
Transfer Characteristics



Gate Charge

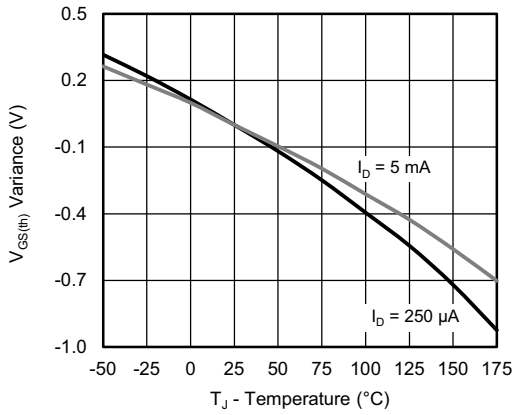


On-Resistance vs. Drain Current

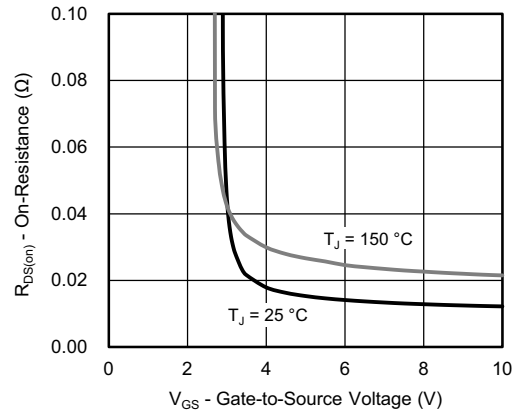


Source Drain Diode Forward Voltage

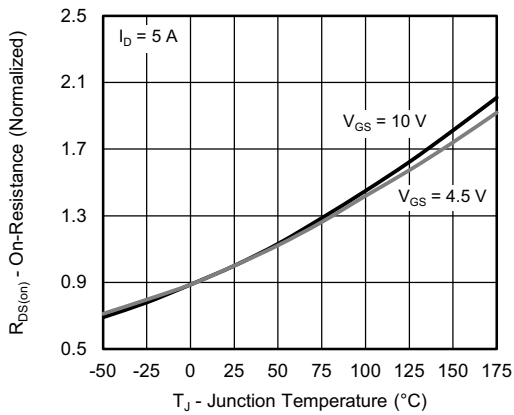
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



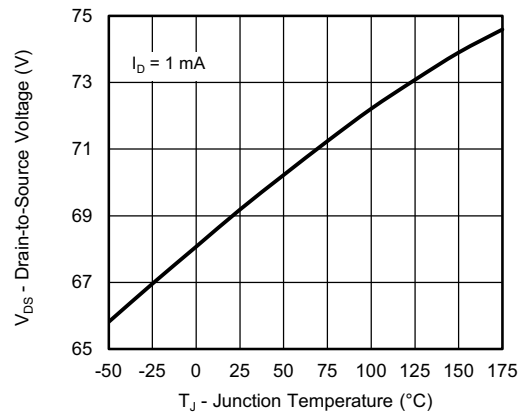
Threshold Voltage



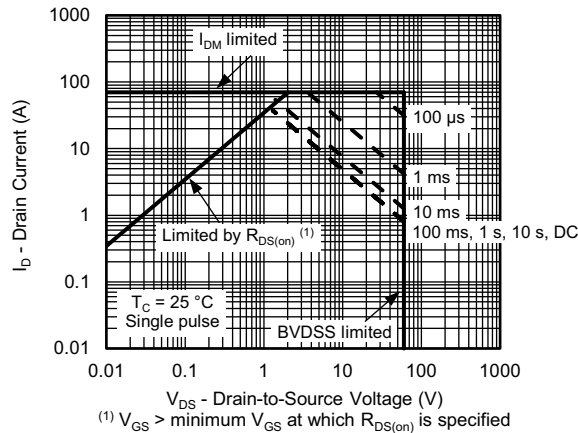
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature

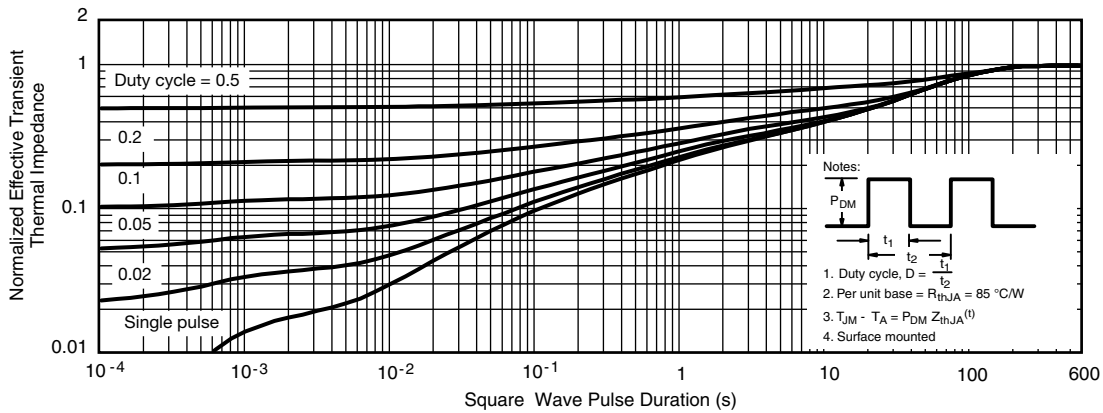


⁽¹⁾ $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

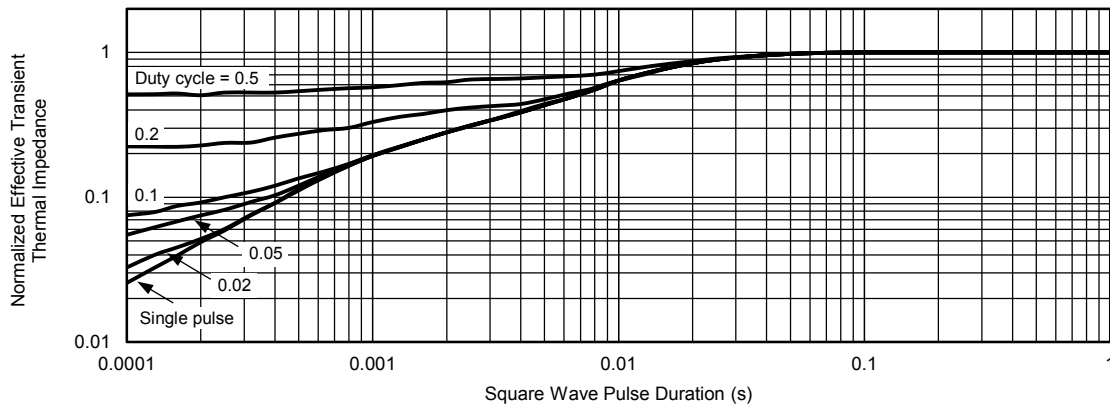
Safe Operating Area



N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 is given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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